BC 327 · BC 328

PNP SILICON AF MEDIUM POWER TRANSISTORS

THE BC327, BC328 ARE PNP SILICON PLANAR EPITAXIAL TRANSISTORS FOR USE IN AF DRIVER AND OUTPUT STAGES, AS WELL AS FOR UNIVERSAL APPLICATIONS. THE BC327, BC328 ARE COMPLEMENTARY TO THE NPN TYPE BC337, BC338 RESPECTIVELY.

CASE TO-92F

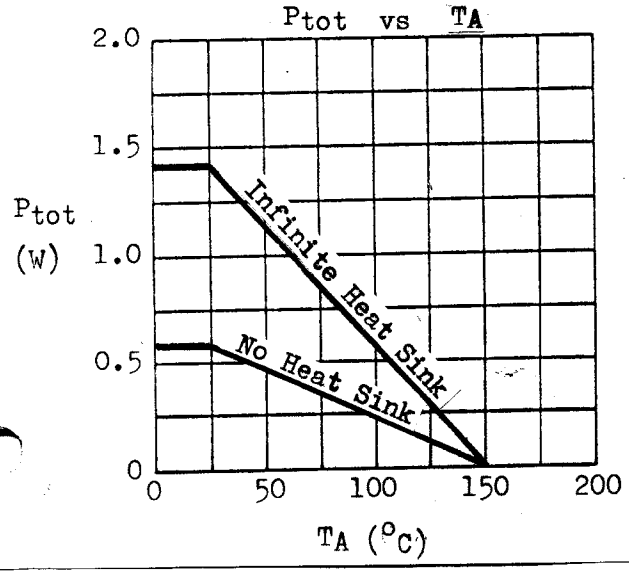
CEB

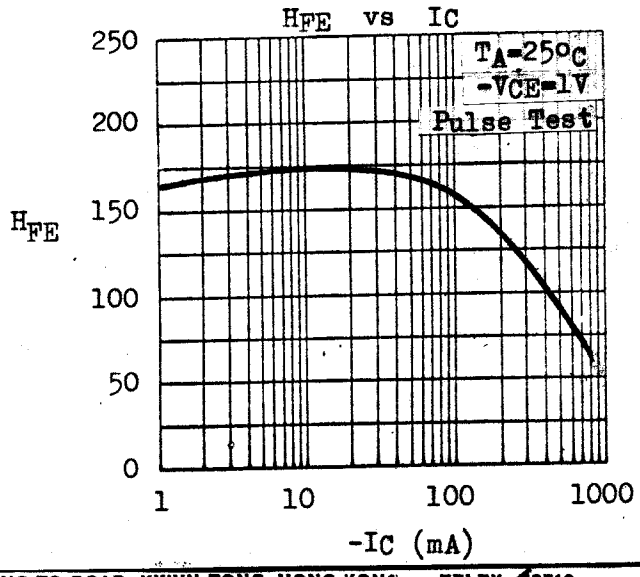
ABSOLUTE MAXIMUM RATINGS

		BC327	BC328
Collector-Emitter Voltage (V_{BE}=0)	$-V_{CES}$	50V	30V
Collector-Emitter Voltage (I_B=0)	$-V_{CEO}$	45V	25V
Emitter-Base Voltage	$-V_{EBO}$	5V	
Collector Current	$-I_C$	0.8A	
Collector Peak Current ($t \leq 10mS$)	$-I_{CM}$	1.5A	
Total Power Dissipation (@ $T_C \leq 25°C$)	P_{tot}	1.4W	
(@ $T_A \leq 25°C$)		625mW	
Operating Junction & Storage Temperature	T_j, T_{stg}	-55 to 150°C	

THERMAL RESISTANCE

Junction to Case	θ_{jc}	90°C/W	max.
Junction to Ambient	θ_{ja}	200°C/W	max.





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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	BC327 MIN	BC327 TYP	BC327 MAX	BC328 MIN	BC328 TYP	BC328 MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	$-BV_{CES}$	50			30			V	$-I_C$=0.1mA V_{BE}=0
Collector-Emitter Breakdown Voltage	$-LV_{CEO}$ *	45			25			V	$-I_C$=10mA I_B=0
Emitter-Base Breakdown Voltage	$-BV_{EBO}$	5			5			V	$-I_E$=0.1mA I_C=0
Collector Cutoff Current	$-I_{CES}$			100				nA	$-V_{CES}$=45V
							100	nA	$-V_{CES}$=25V
				10				µA	$-V_{CES}$=45V T_A=125°C
							10	µA	$-V_{CES}$=25V T_A=125°C
Collector-Emitter Saturation Voltage	$-V_{CE(sat)}$*			0.7			0.7	V	$-I_C$=500mA $-I_B$=50mA
Base-Emitter Voltage	$-V_{BE}$ *			1.2			1.2	V	$-I_C$=300mA -VCE=1V
D.C. Current Gain	H_{FE} *	100		630	100		630		$-I_C$=100mA -VCE=1V
Group 16		100		250	100		250		
Group 25		160		400	160		400		
Group 40		250		630	250		630		
All Groups		40			40				$-I_C$=300mA -VCE=1V
Matched Pair Ratio	$\frac{H_{FE\ 1}}{H_{FE\ 2}}$ *			1.41			1.41		$-I_C$=100mA -VCE=1V
Current Gain-Bandwidth Product	f_T		100			100		MHz	$-I_C$=10mA -VCE=5V
Collector-Base Capacitance	C_{ob}		14			14		pF	$-V_{CB}$=10V I_E=0 f=1MHz

* Pulse Test : Pulse Width=0.3mS, Duty Cycle=1%